

ABSTRACT

A thin film formation method in accordance with the present invention forms banks (110) where affinity bank layers and non-affinity bank layers are alternately layered by repeating a step of forming an affinity bank layer (111 - 11n) with a material having affinity for a thin film material solution (130) (such inorganic material as SiO_2) and a step of forming a non-affinity bank layer (121 - 12n) with a material having non-affinity for the thin film material solution (130) (such organic material as resist) one or more times. Finally the thin film material solution (130) is filled between banks by an ink jet method, heat treatment is executed, and a thin film layer (131 - 13n) is sequentially layered. By these steps, cost required for affinity control can be decreased and forming multi-layer thin films with uniform film thickness becomes possible.